Practice Final Exam – ECG 721 Memory Circuit Design, Final Exam University of Nevada, Las Vegas

NAME:

- Show your work to get credit.
- Open book and closed notes.
- Show your work on the attached sheets of paper in order and on one side only in a neat manner.
- Do not do work on these test sheets.
- Turn this test sheet in with your test. Failing to return this sheet will result in a 0 on the exam.
- 1. Explain how signal-to-noise ratio is determined by the memory-bit and bit-line capacitances in a DRAM. (5 points)
- 2. Sketch the schematics for a bitline pair in a folded DRAM architecture with the n-sense amp, p-sense amp, equilibration circuitry, and I/O devices. Sketch, and label what's going on, the voltage signals used during a read operation. (10 points)
- 3. What is the biggest concern with increasing the number of rows in a memory array? with increasing the number of columns? (5 points)
- 4. Why do we need to ensure that the parasitic bitline capacitances connected to a sense amplifier are balanced? (10 points)
- 5. Sketch the layouts of DRAM cells used in both folded and open arrays. Comment on the pros and cons of each layout. (5 points)
- 6. From a circuit designer's point of view what is the difference between CHE and FNT? (10 points)
- 7. Sketch a sense amplifier useful for regenerating logic levels outside of the array (on the side opposite the I/O devices) in a memory. Sometimes this sense amplifier is called a helper flip-flop. Using this topology discuss kickback noise, clock feedthrough, how the previous comparison's results (memory) is erased, and how power is minimized. (20 points)
- 8. Sketch the schematic of a 6T SRAM memory cell. Describe why you need to precharge the bitlines high. (5 points)
- 9. Sketch the IV curves for an erased and a programmed Flash memory cells and describe the state of charge on the floating gate in your own words. (5 points)
- 10. Explain, in your own words, why a VCO is represented as an integration when analyzing PLLs. (5 points)
- 11. Sketch the schematic of a delta-sigma sensing circuit useful for determining the value of a capacitor based upon the delta-sigma techniques from Ch. 17. Discuss the operation and derive equations governing the circuit's operation. (20 points).